

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	700mΩ@4.5V	500mA
	850mΩ@2.5V	

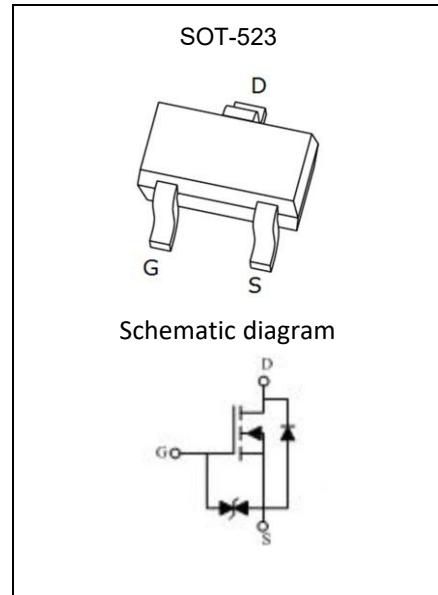
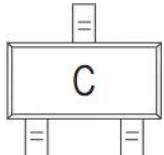
Feature

- High-Side Switching
- Low On-Resistance
- Low Threshold
- Fast Switching Speed
- ESD Protected

Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	500	mA
Pulsed Drain Current ¹	I_{DM}	1000	
Power Dissipation ²	P_D	150	mW
Maximum Power Dissipation ³		275	
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	



SALLTECH

SR1012

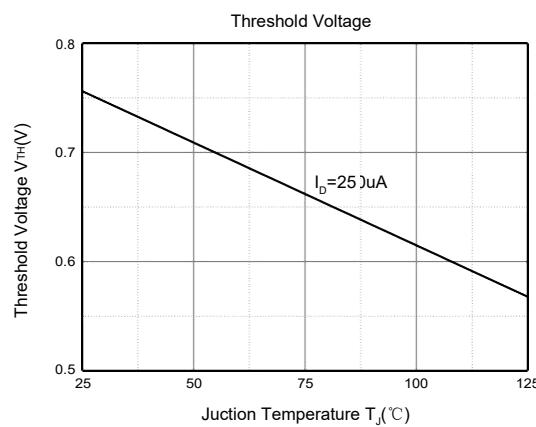
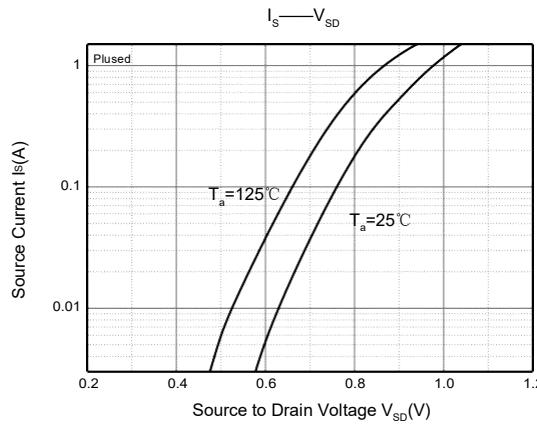
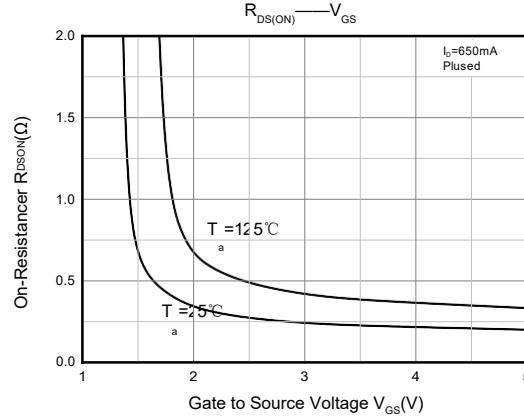
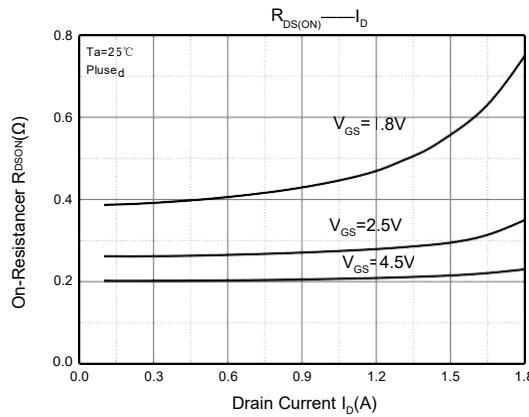
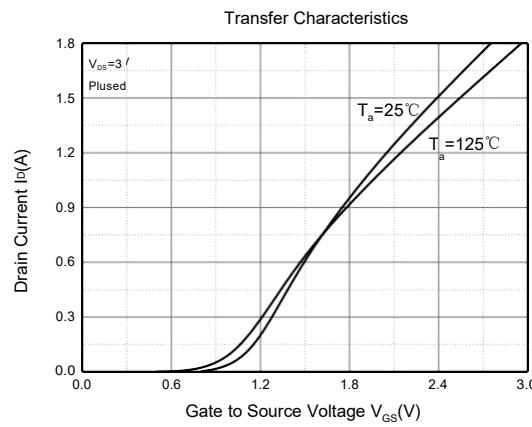
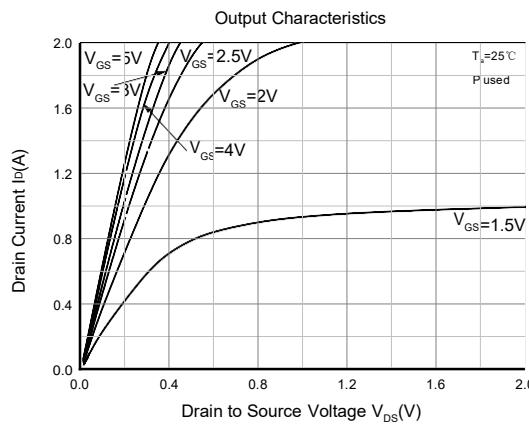
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 16\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 4.5\text{V}, V_{\text{DS}} = 0\text{V}$			± 1	μA
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	0.45	0.75	1.2	V
Drain-source on-resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 600\text{mA}$		190	700	$\text{m}\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_D = 500\text{mA}$		260	850	
Forward transconductance	g_{FS}	$V_{\text{DS}} = 10\text{V}, I_D = 400\text{mA}$	1			S
Dynamic characteristics⁴						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 16\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$			120	pF
Output Capacitance	C_{oss}				20	
Reverse Transfer Capacitance	C_{rss}				15	
Switching Characteristics⁴						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 10\text{V}, I_D = 500\text{mA}, V_{\text{GS}} = 4.5\text{V}, R_G = 10\Omega$		6.7		ns
Turn-on rise time	t_r			4.8		ns
Turn-off delay time	$t_{\text{d}(\text{off})}$			17.3		ns
Turn-off fall time	t_f			7.4		ns
Source-Drain Diode characteristics						
Diode Forward voltage ⁵	V_{DS}	$I_S = 0.15\text{A}, V_{\text{GS}} = 0\text{V}$			1.2	V

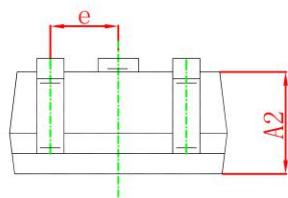
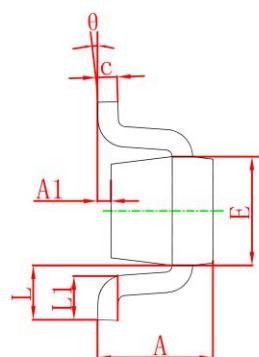
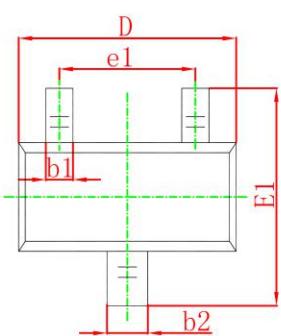
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at $T_a=25^\circ\text{C}$.
3. This test is performed with infinite heat sink at $T_c=25^\circ\text{C}$.
4. These parameters have no way to verify.
5. Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Typical Electrical and Thermal Characteristics



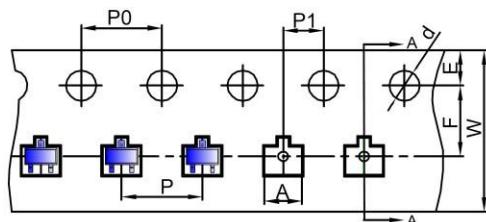
SOT-523 Package Information



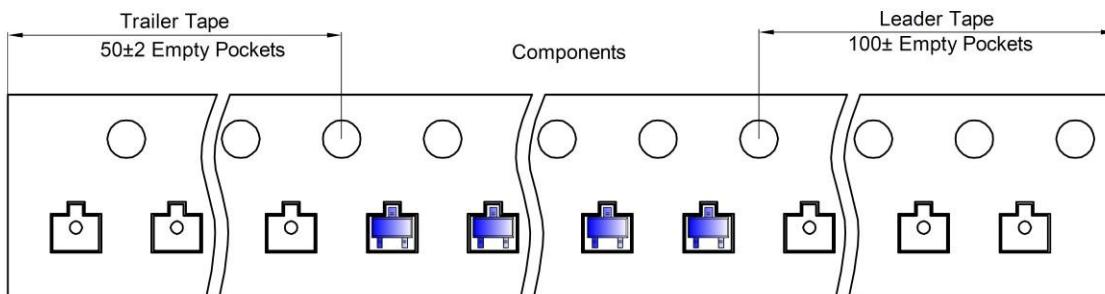
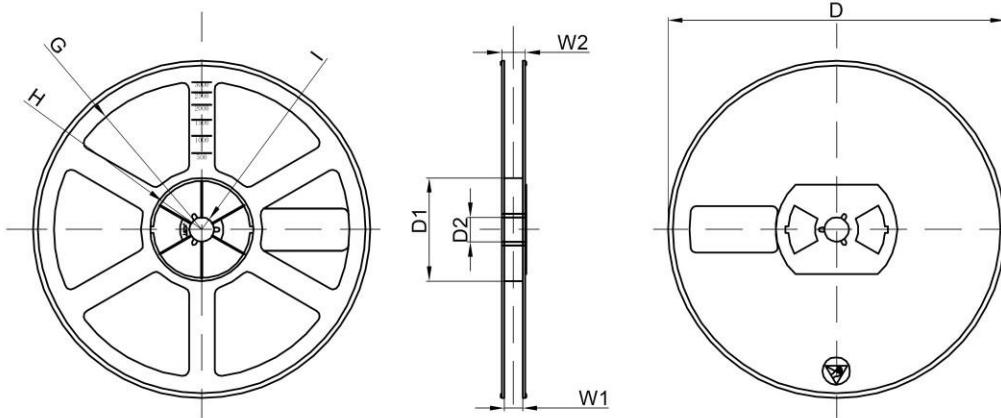
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-523 Tape and Reel**SOT-523 Tape and reel**

SOT-523 Embossed Carrier Tape



Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-523	1.85	1.85	0.875	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-523 Tape Leader and Trailer**SOT-523 Reel**

Dimensions are in millimeter							
Reel Option	D	D1	D2	G	H	I	W1
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50
							12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	